

CY7C199CN

256-Kbit (32 K × 8) Static RAM

Features

- Fast access time: 15 ns
- Wide voltage range: 5.0 V ± 10% (4.5 V to 5.5 V)
- complementary metal oxide semiconductor (CMOS) for optimum speed and power
- Transistor transistor logic (TTL) compatible inputs and outputs
- 2.0 V data retention
- Low CMOS standby power
- Automated power-down when deselected
- Available in Pb-free 28-pin molded small outline J-lead (SOJ) and 28-pin DIP packages

Logic Block Diagram

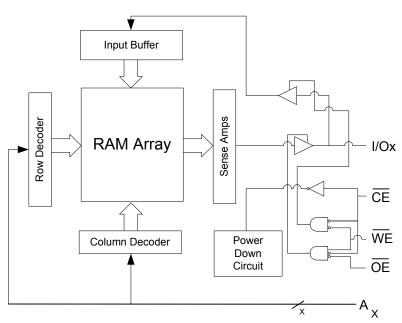
General Description

The CY7C199CN^[1] is a high performance CMOS Asynchronous SRAM organized as 32K by 8 bits that supports an asynchronous memory interface. The device features an automatic power-down feature that reduces power consumption when deselected.

See the Truth Table on page 4 in this data sheet for a complete description of read and write modes.

The CY7C199CN is available in 28-pin molded SOJ and 28-pin DIP package(s).

For a complete list of related documentation, click here.



Product Portfolio

Description	-15	Unit
Maximum access time	15	ns
Maximum operating current	80	mA
Maximum CMOS standby current (low power)	500	μA

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CY7C199CN

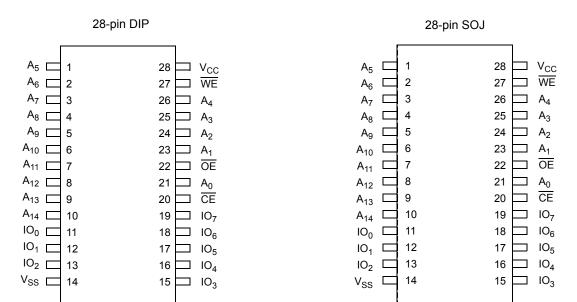
Contents

Pin Layout and Specifications	3
Pin Description	
Truth Table	
Maximum Ratings	
Operating Range	5
DC Electrical Characteristics	5
Capacitance	6
Thermal Resistance	
AC Test Loads	6
AC Test Conditions	6
Data Retention Characteristics	7
Data Retention Waveform	7
AC Electrical Characteristics	

Ordering Information	. 12
Ordering Code Definitions	. 12
Package Diagrams	. 13
Acronyms	. 15
Document Conventions	. 15
Units of Measure	. 15
Document History Page	. 16
Sales, Solutions, and Legal Information	. 17
Worldwide Sales and Design Support	. 17
Products	. 17
PSoC® Solutions	. 17
Cypress Developer Community	. 17
Technical Support	



Pin Layout and Specifications



Pin Description

Pin	Туре	Description	DIP	SOJ
A _X	Input	Address inputs	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 21, 23, 24, 25, 26	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 21, 23, 24, 25, 26
CE	Control	Chip Enable	20	20
IO _X	Input or Output	Data input outputs	11, 12, 13, 15, 16, 17, 18, 19	11, 12, 13, 15, 16, 17, 18, 19
OE	Control	Output enable	22	22
V _{CC}	Supply	Power (5.0 V)	28	28
V _{SS}	Supply	Ground	14	14
WE	Control	Write Enable	27	27

Note

1. For best practices recommendations, refer to the Cypress application note System Design Guidelines on www.cypress.com.



Truth Table

CE	OE	WE	IOx	Mode	Power
н	Х	Х	High-Z	Deselect/Power-down	Stand by (I _{SB})
L	L	Н	Data Out	Read	Active (I _{CC})
L	Х	L	Data In	Write	Active (I _{CC})
L	Н	Н	High-Z	Selected, Outputs disabled	Active (I _{CC})



Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Parameter ^[2]	Description	Value	Unit
T _{STG}	Storage temperature	–65 to +150	°C
T _{AMB}	Ambient temperature with power applied (that is, case temperature)	–55 to +125	°C
V _{CC}	Core Supply voltage relative to V _{SS}	–0.5 to +7.0	V
V _{IN} , V _{OUT}	DC voltage applied to any pin relative to V _{SS}	–0.5 to V _{CC} + 0.5	V
I _{OUT}	Output short-circuit current	20	mA
V _{ESD}	Static discharge voltage (in accordance with MIL-STD-883, Method 3015)	> 2001	V
I _{LU}	Latch-up current	> 200	mA

Operating Range

Range	Ambient Temperature (T _A)	Voltage Range (V _{CC})
Commercial	0 °C to 70 °C	5.0 V ± 10%
Industrial	–40 °C to 85 °C	5.0 V ± 10%

DC Electrical Characteristics

Over the Operating Range

Parameter [2]	Description	Condition	Condition		-15	
Farameter	Description	Condition			Max	Unit
V _{IH}	Input HIGH voltage			2.2	V _{CC} + 0.3	V
V _{IL}	Input LOW voltage			-0.5	0.8	V
V _{OH}	Output HIGH voltage	V_{CC} = Min, I_{OH} = -4.0 mA		2.4	-	V
V _{OL}	Output LOW voltage	V_{CC} = Min, I _{OL} = 8.0 mA		-	0.4	V
I _{CC}	V _{CC} Operating supply current	V_{CC} = Max, I _{OUT} = 0 mA, f = F _{max} = 1/t _{RC}		-	80	mA
I _{SB1}	Automatic CE power-down	$Max V_{CC}, \overline{CE} \ge V_{IH},$		-	30	mA
	current – TTL inputs	$V_{IN} \ge V_{IH}$ or $V_{IN} \le V_{IL}$, f = F _{max}	L	-	10	mA
I _{SB2}	Automatic CE power-down	$Max V_{CC}, \overline{CE} \ge V_{CC} - 0.3 V,$		-	10	mA
	current – CMOS Inputs	$V_{IN} \ge V_{CC} - 0.3 \text{ V}, \text{ or } V_{IN} \le 0.3 \text{ V}, \text{ f} = 0$	L	-	500	μA
I _{OZ}	Output leakage current	$GND \le V_I \le V_{CC}$, output disabled		-5	+5	μA
I _{IX}	Input leakage current	$GND \le V_I \le V_{CC}$		-5	+5	μΑ



Capacitance

Parameter ^[3]	Description	Conditions	Мах	Unit
C _{IN}	Input capacitance	T _A = 25 °C, f = 1 MHz, V _{CC} = 5.0 V	8	pF
C _{OUT}	Output capacitance		8	

Thermal Resistance

Parameter ^[3]	Description	Conditions	SOJ	DIP	Unit
θ_{JA}		Still air, soldered on a 3 × 4.5 square inch, two–layer printed circuit board	79	69.33	°C/W
θ ^{JC}	Thermal resistance (junction to case)		41.42	31.62	

AC Test Loads

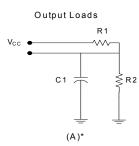
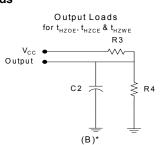
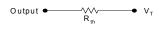


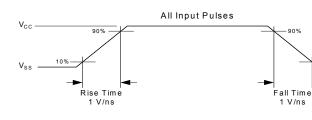
Figure 1. AC Test Loads



10%

Thevenin Equivalent





* including scope and jig capacitance

AC Test Conditions

Parameter	Description	Nom	Unit
C1	Capacitor 1	30	pF
C2	Capacitor 2	5	
R1	Resistor 1	480	Ω
R2	Resistor 2	255	1
R3	Resistor 3	480	
R4	Resistor 4	255	1
R _{TH}	Resistor Thevenin	167	
V _{TH}	Voltage Thevenin	1.73	V

Note

3. Tested initially and after any design or process change that may affect these parameters.

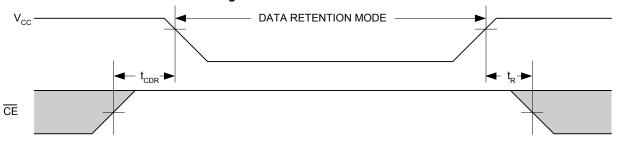


Data Retention Characteristics

Parameter ^[4]	Description	Condition	Min	Max	Unit
V _{DR}	V _{CC} for data retention		2.0	-	V
I _{CCDR}	Data retention current	$\begin{array}{l} V_{CC} = V_{DR} = 2.0 \text{ V}, \ \overline{CE} \geq V_{CC} - 0.3 \text{ V}, \\ V_{IN} \geq V_{CC} - 0.3 \text{ V} \text{ or } V_{IN} \leq 0.3 \text{ V} \end{array}$	_	150	μA
	Chip deselect to data retention time	$V_{IN} \ge V_{CC} - 0.3 \text{ V or } V_{IN} \le 0.3 \text{ V}$	0	-	ns
t _R	Operation recovery time		200	-	μS

Data Retention Waveform

Figure 2. Data Retention Waveform





AC Electrical Characteristics

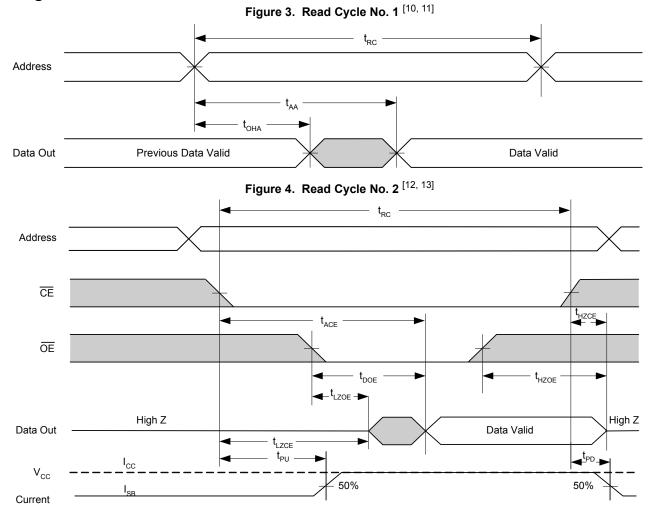
Parameter ^[5, 6]	Description	-15		Unit
	Description		Max	
t _{RC}	Read cycle time	15	-	ns
t _{AA}	Address to data valid	-	15	ns
t _{OHA}	Data hold from address change	3	-	ns
t _{ACE}	CE to data valid	-	15	ns
t _{DOE}	OE to data valid	-	7	ns
t _{LZOE}	OE to Low-Z ^[7]	0	_	ns
t _{HZOE}	OE to High-Z ^[7, 8]	-	7	ns
t _{LZCE}	CE to Low-Z ^[7]	3	_	ns
t _{HZCE}	CE to High-Z ^[7, 8]	-	7	ns
t _{PU}	CE to Power-up	0	_	ns
t _{PD}	CE to Power-down	-	15	ns
t _{WC}	Write Cycle Time ^[9]	15	_	ns
t _{SCE}	CE to write end		_	ns
t _{AW}	Address setup to write end	10	_	ns
t _{HA}	Address hold from write end	0	_	ns
t _{SA}	Address setup to write start	0	_	ns
t _{PWE}	WE pulse width	9	_	ns
t _{SD}	Data setup to write end	9	_	ns
t _{HD}	Data hold from write end		_	ns
t _{HZWE}	WE LOW to High-Z ^[7, 8]	-	7	ns
t _{LZWE}	WE HIGH to Low-Z ^[7]	3	_	ns

Notes

- Test Conditions are based on a transition time of 3 ns or less and timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0 V.
 The minimum write cycle pulse width for Write Cycle No. 3 (WE Controlled, OE LOW) should be equal to sum of t_{SD} and t_{HZWE}.
 At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
 t_{HZOE}, t_{HZCE}, t_{HZWE} are specified as in part (b) of the Figure 1 on page 6. Transitions are measured ± 200 mV from steady state voltage.
 The stand the sum of th
- 9. The internal memory write time is defined by the overlap of CE LOW and WE LOW. CE and WE must be LOW to initiate a write, and the transition of any of these signals can terminate the write. The input data setup and hold timing must be referenced to the leading edge of the signal that terminates the write.



Timing Waveforms



Notes

10. Device is continuously selected. $\overline{OE} = V_{IL} = \overline{CE}$. 11. WE is HIGH for read cycle. 12. This cycle is \overline{OE} controlled and \overline{WE} is HIGH read cycle.

13. Address valid before or similar with \overline{CE} transition LOW.



Timing Waveforms (continued)

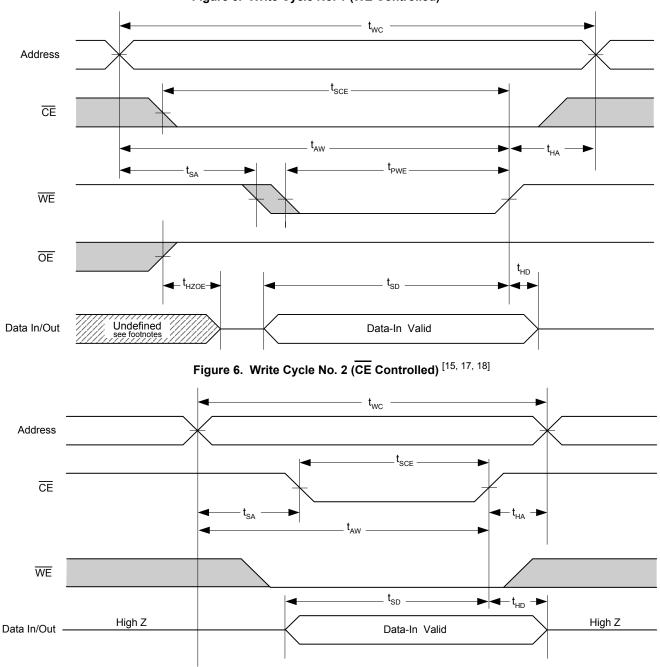


Figure 5. Write Cycle No. 1 (WE Controlled) ^[14, 15, 16]

Notes

14. This cycle is $\overline{\text{WE}}$ controlled, $\overline{\text{OE}}$ is HIGH during write.

15. Data in and/or out is high impedance if $\overline{OE} = V_{IH}$.

16. During this period the IOs are in output state and input signals must not be applied.

17. This cycle is CE controlled.

18. If CE goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.



Timing Waveforms (continued)

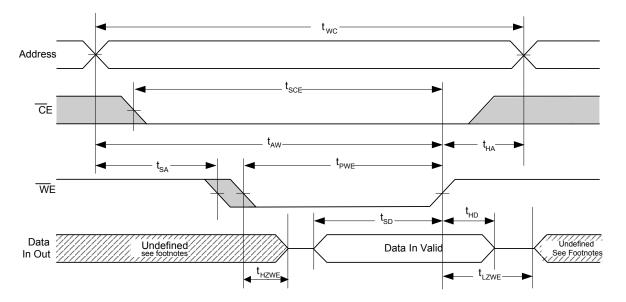


Figure 7. Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW) ^[19]



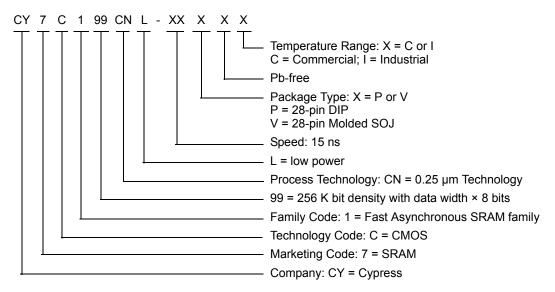


Ordering Information

Contact local sales representative regarding availability of these parts.

Speed (ns)	Ordering Code	Package Diagram	Package Type	Power Option	Operating Range
15	CY7C199CN-15PXC	51-85014	28-pin DIP (6.9 × 35.6 × 3.5 mm), Pb-free	Standard	Commercial
	CY7C199CNL-15VXI	51-85031	28-pin (300-Mil) Molded SOJ, Pb-free	Low Power	Industrial

Ordering Code Definitions





Package Diagrams

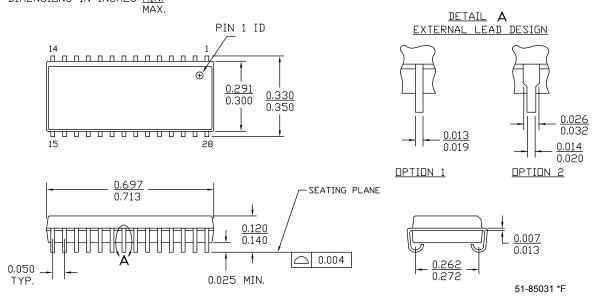
Figure 8. 28-pin SOJ (300 Mils) V28.3 Package Outline, 51-85031

28 Lead (300 Mil) Molded SOJ V21

NDTE :

- 1, JEDEC STD REF MOO88
- 2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH

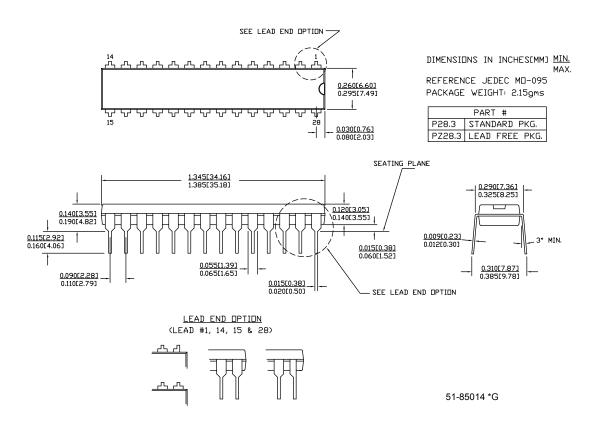
MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.006 in (0.152 mm) PER SIDE 3. DIMENSIONS IN INCHES MIN.





Package Diagrams (continued)







Acronyms

Acronym	Description
CE	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
OE	Output Enable
SRAM	Static Random Access Memory
SOJ	Small Outline J-lead
VFBGA	Very Fine-Pitch Ball Grid Array
WE	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure	
°C	degree Celsius	
MHz	megahertz	
μA	microampere	
mA	milliampere	
mV	millivolt	
mW	milliwatt	
ns	nanosecond	
pF	picofarad	
V	volt	
W	watt	



Document History Page

Document Title: CY7C199CN, 256-Kbit (32 K × 8) Static RAM Document Number: 001-06435				
Revision	ECN	Submission Date	Orig. of Change	Description of Change
**	430363	See ECN	NXR	New data sheet.
*A	684342	See ECN	VKN	Added Automotive-A Information Updated Ordering Information Table
*B	839904	See ECN	VKN	Added t _{DOE} spec for Automotive-A part in AC Electrical characteristics table
*C	2896044	03/19/2010	NXR	Updated Ordering Information Table Updated Package Diagram
*D	3108898	12/13/2010	PRAS	Added Ordering Code Definitions.
*E	3198636	03/17/11	PRAS	Dislodged Automotive device information to 001-67737 Updated template and styles.
*F	3246329	05/04/2011	PRAS	Additional information on ISB1, ISB2 with respect to L parts
*G	3302830	08/02/2011	RAME	Removed all information related to 28-pin TSOP 1. Removed all information related to 20 ns speed bin. Removed the following parts from ordering information table. CY7C199CN-15VXC CY7C199CN-20ZXI Removed spec 51-85071.
*H	4318563	03/25/2014	VINI	Updated Package Diagrams: spec 51-85014 – Changed revision from *F to *G. Updated to new template. Completing Sunset Review.
*	4546472	10/28/2014	VINI	Updated Maximum Ratings: Referred Note 2 in "Parameter" column. Updated AC Electrical Characteristics: Added Note 6 and referred the same note in "Parameter" column.
*J	4576406	01/16/2015	VINI	Added related documentation hyperlink in page 1. Updated Figure 8 in Package Diagrams (spec 51-85031 *E to *F).



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